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March 1996



### NDS355N N-Channel Logic Level Enhancement Mode Field Effect Transistor

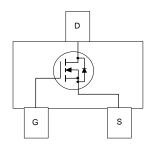
#### **General Description**

These N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage applications in notebook computers, portable phones, PCMICA cards, and other battery powered circuits where fast switching, and low in-line power loss are needed in a very small outline surface mount package.

#### Features

- 1.6A, 30V.  $R_{DS(ON)} = 0.125\Omega$  @  $V_{GS} = 4.5V$ .
- Proprietary package design using copper lead frame for superior thermal and electrical capabilities.
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- Exceptional on-resistance and maximum DC current capability.
- Compact industry standard SOT-23 surface mount package.



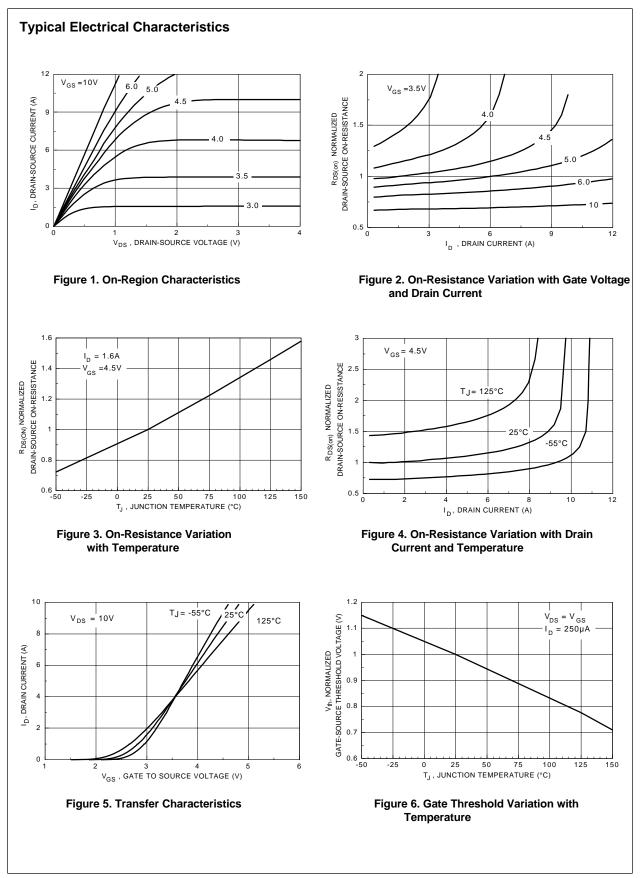


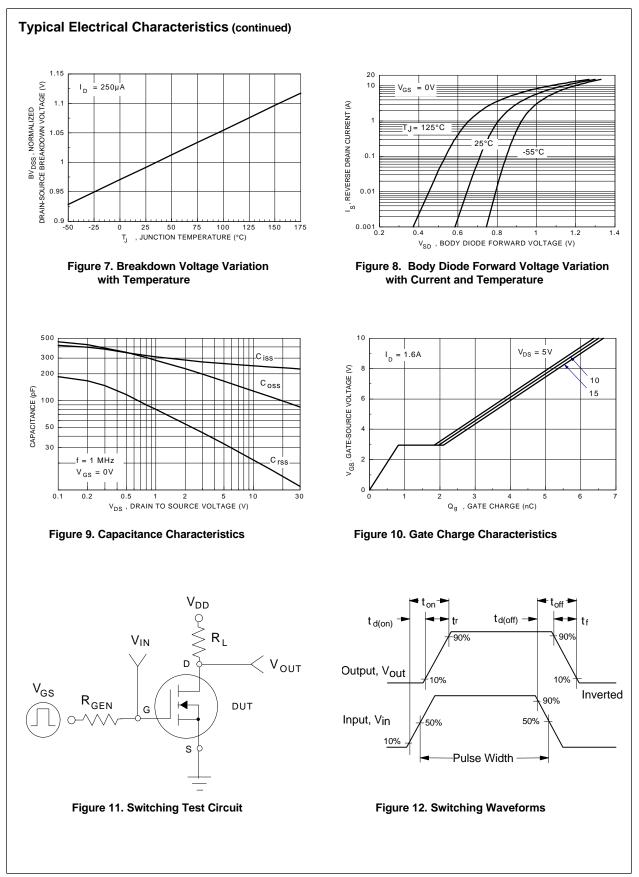
#### **Absolute Maximum Ratings** $T_{A} = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	NDS355N	Units
V <sub>DSS</sub>	Drain-Source Voltage	30	V
V <sub>GSS</sub>	Gate-Source Voltage - Continuous	20	V
I <sub>D</sub>	Drain Current - Continuous (Note 1a)	± 1.6	А
	- Pulsed	± 10	
P <sub>D</sub>	Maximum Power Dissipation (Note 1a)	0.5	W
	(Note 1b)	0.46	
T_,T <sub>stg</sub>	Operating and Storage Temperature Range	-55 to 150	°C
THERMA	L CHARACTERISTICS		
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	°C/W
R <sub>øJC</sub>	Thermal Resistance, Junction-to -Case (Note 1)	75	°C/W

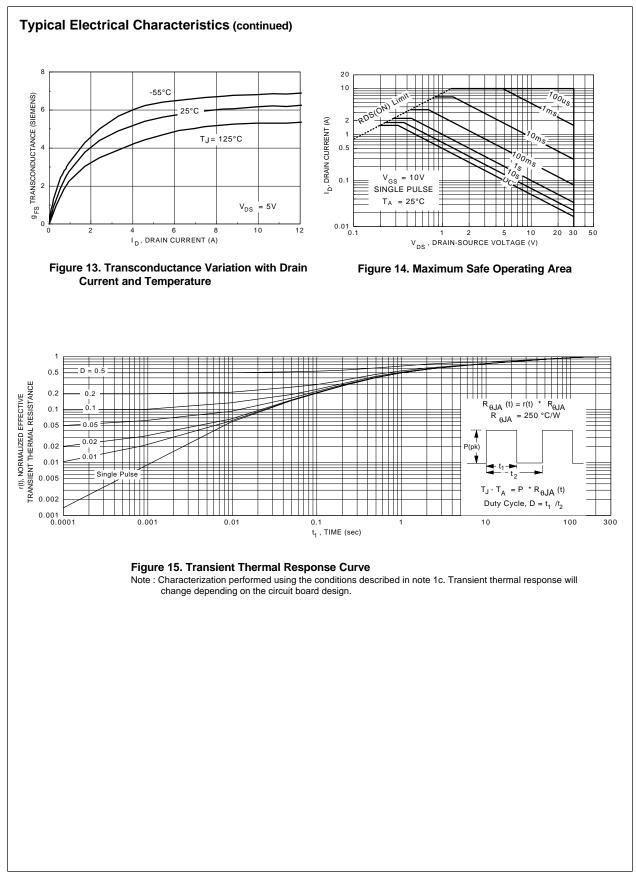
Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHA	RACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$		30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$				1	μA
			T_=125°C			10	μA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -12 V, V_{DS} = 0 V$				-100	nA
	ACTERISTICS (Note 2)	·					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$		1	1.6	2	V
			T_=125°C	0.5	1.3	1.5	1
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 1.6 \text{ A}$	<u>.</u>			0.125	Ω
			T_=125°C			0.25	1
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 1.9 \text{ A}$	<u>.</u>			0.085	
D(ON)	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$		6			Α
9 <sub>FS</sub>	Forward Transconductance	$V_{\rm DS} = 5 \text{ V}, \text{ I}_{\rm D} = 1.6 \text{ A}$			3.5		S
DYNAMIC	CHARACTERISTICS						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			245		pF
C <sub>oss</sub>	Output Capacitance				130		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				20		pF
SWITCHIN	IG CHARACTERISTICS (Note 2)						
D(on)	Turn - On Delay Time	$V_{\text{DD}} = 10 \text{ V}, \text{ I}_{\text{D}} = 1 \text{ A}, \\ V_{\text{GS}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$			15	30	ns
ţ	Turn - On Rise Time				14	30	ns
D(off)	Turn - Off Delay Time				12	25	ns
f	Turn - Off Fall Time				4	10	ns
J <sup>ª</sup>	Total Gate Charge	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1.6 \text{ A},$			3.5	5	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 5 V$				1	nC
Q <sub>gd</sub>	Gate-Drain Charge					2	nC

Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRAIN-SO	URCE DIODE CHARACTERISTICS AN	ID MAXIMUM RATINGS				
ls	Maximum Continuous Source Current				0.6	Α
I <sub>SM</sub>	Maximum Pulse Source Current (Note 2)			6	Α	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = 1.6 A$		0.8	1.2	V
$P_{D}(t) = \frac{T_{J}}{R_{0}}$ Typical R <sub>0</sub> M a. 250°C/W b.	a R <sub>gick</sub> is determined by the user's board design. $\frac{J-T_A}{a_UA^0} = \frac{T_A-T_A}{R_{6U}dR_{6C}(A^{\prime})} = l_D^2(1) × R_{DS(CM)}   \theta_{T_U} $ using the board layouts shown below on 4.5'x5" FR-4 PC when mounted on a 0.02 in <sup>2</sup> pad of 2oz cpper. 270°C/W when mounted on a 0.001 in <sup>2</sup> pad of 2oz cpper. <b>1</b> <b>1</b> <b>1</b> <b>1</b> <b>1</b> <b>1</b> <b>1</b> <b>1</b>					





NDS355N Rev. D1



NDS355N Rev. D1

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